

ZXM66P03N8

30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.025\Omega$; $I_D = -7.9A$

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

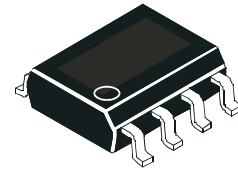
- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

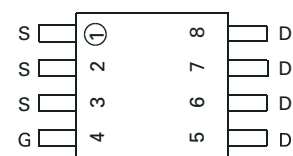
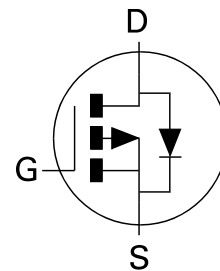
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXM66P03N8TA	7"	12mm	500 units
ZXM66P03N8TC	13"	12mm	2500 units

DEVICE MARKING

- ZXM
66P03



SO8



Top View

ZXM66P03N8

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=-10V$; $T_A=25^{\circ}C$ (b) $V_{GS}=-10V$; $T_A=70^{\circ}C$ (b) $V_{GS}=-10V$; $T_A=25^{\circ}C$ (a)	I_D	-7.9 -6.3 -6.25	A
Pulsed Drain Current (c)	I_{DM}	-28	A
Continuous Source Current (Body Diode)(b)	I_S	-4.1	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	-28	A
Power Dissipation at $T_A=25^{\circ}C$ (a) Linear Derating Factor	P_D	1.56 12.5	W mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b) Linear Derating Factor	P_D	2.5 20	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	80	$^{\circ}C/W$
Junction to Ambient (b)	$R_{\theta JA}$	50	$^{\circ}C/W$

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
 (b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.
 (c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.05$, pulse width 10 μs - pulse width limited by maximum junction temperature.

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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	V _{DS} =-24V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			-100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	I _D =-250μA, V _{DS} =V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.025 0.035	Ω Ω	V _{GS} =-10V, I _D =-5.6A V _{GS} =-4.5V, I _D =-2.8A
Forward Transconductance (1)(3)	g _{fs}		14.4		S	V _{DS} =-15V,I _D =-5.6A
DYNAMIC (3)						
Input Capacitance	C _{iss}		1979		pF	V _{DS} =-25 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{Oss}		743		pF	
Reverse Transfer Capacitance	C _{rss}		279		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		7.6		ns	V _{DD} =-15V, I _D =-5.6A R _G =6.2Ω, V _{GS} =-10V
Rise Time	t _r		16.3		ns	
Turn-Off Delay Time	t _{d(off)}		94.6		ns	
Fall Time	t _f		39.6		ns	
Gate Charge	Q _g		36		nC	V _{DS} =-15V,V _{GS} =-5V I _D =-5.6A
Total Gate Charge	Q _g		62.5		nC	V _{DS} =-15V,V _{GS} =-10V I _D =-5.6A
Gate-Source Charge	Q _{gs}		4.9		nC	
Gate Drain Charge	Q _{gd}		19.6		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			-0.95	V	T _j =25°C, I _S =-5.6A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		35		ns	T _j =25°C, I _F =-5.6A, di/dt= 100A/μs
Reverse Recovery Charge(3)	Q _{rr}		39.9		nC	

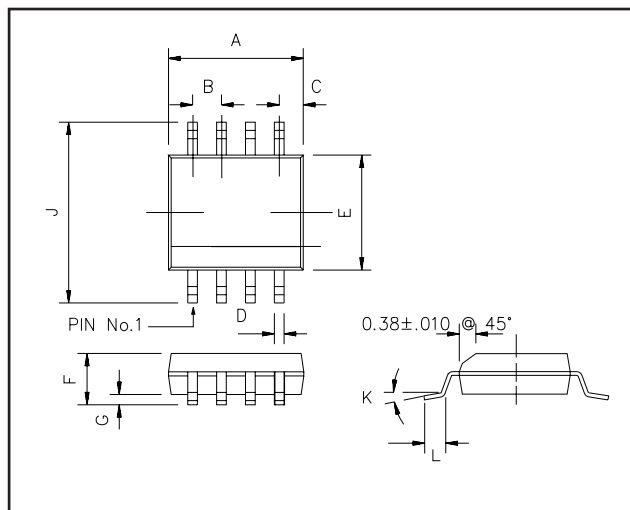
(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.

(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

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PACKAGE DIMENSIONS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	4.80	4.98	0.189	0.196
B	1.27 BSC		0.05 BSC	
C	0.53 REF		0.02 REF	
D	0.36	0.46	0.014	0.018
E	3.81	3.99	0.15	0.157
F	1.35	1.75	0.05	0.07
G	0.10	0.25	0.004	0.010
J	5.80	6.20	0.23	0.24
K	0°	8°	0°	8°
L	0.41	1.27	0.016	0.050

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